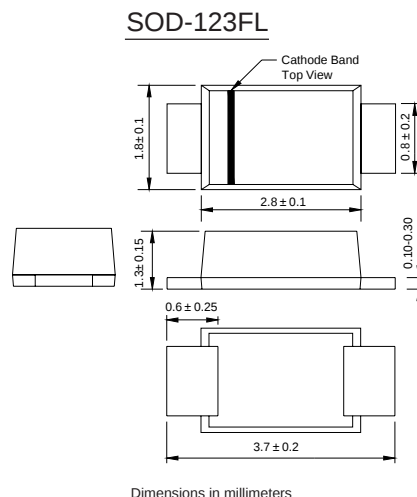


2 A low VF MEGA Schottky barrier rectifier

Features

- Metal to silicon rectifier, majority carrier conduction.
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications.
- Low power loss, high efficiency.
- High current capability, low V_F .
- High surge capacity.
- Glass passivated



Schottky Rectifiers

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

CHARACTERISTICS	SYMBOL	PMEG4020EP								UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40								V
Maximum RMS Voltage	V _{RMS}	28								V
Maximum DC Blocking Voltage	V _{DC}	40								V
Maximum Average Forward Rectified Current @T _L =100 °C	I _(AV)	2.0								A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed On Rated Load (JEDEC Method)	I _{FSM}	60								A
Maximum Forward Voltage at 2.0A DC	V _F	0.45	0.5	0.55	0.7	0.85	0.92	0.95	V	
Maximum DC Reverse Current @T _J =25°C	I _R	1.0								mA
at Rated DC Blocking Voltage @T _J =100°C		20								
Typical Junction Capacitance (Note1)	C _J	200								pF
Typical Thermal Resistance (Note2)	R _{θJL}	15								°C/W
Operating Temperature Range	T _J	-55 to +150								°C
Storage Temperature Range	T _{STG}	-55 to + 150								°C

FIG.1– PEAK FORWARD SURGE CURRENT

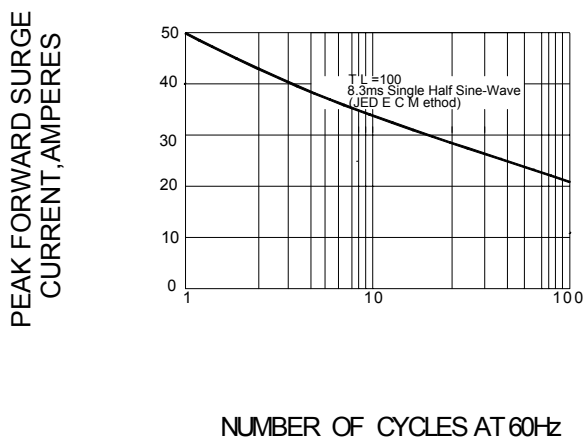


FIG.2 – TYPICAL FORWARD CHARACTERISTICS

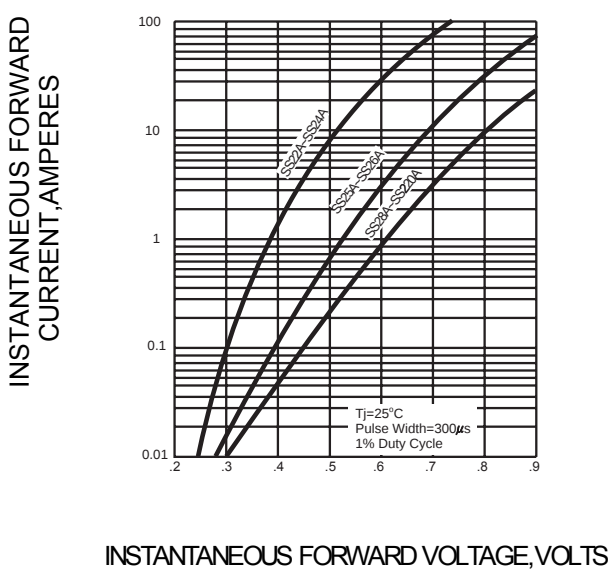


FIG.3 – TYPICAL REVERSE CHARACTERISTICS

